

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|--------|--|--|------------------|
| 1 | BRS | L2 | 108799 | 257/\$.ccls. substrate with insulat\$3 with conductive with semi\$1conductor | USPAT | 2003/08/03 15:03 |
| 2 | BRS | L3 | 108799 | 257/\$.ccls. (substrate with insulat\$3 with conductive with semi\$1conductor) | USPAT | 2003/08/03 15:05 |
| 3 | BRS | L4 | 108490 | 257/\$.ccls. (substrate with insulating with conductive with semi\$1conductor) | USPAT | 2003/08/03 15:06 |
| 4 | BRS | L5 | 107809 | 257/\$.ccls. ((insulating adj substrate) with (conductive adj substrate)) | USPAT | 2003/08/03 15:08 |
| 5 | BRS | L1 | 5739 | substrate with insulat\$3 with conductive with semi\$1conductor | USPAT | 2003/08/03 15:13 |
| 6 | BRS | L6 | 175 | (insulating adj substrate) with (conductive adj substrate) | USPAT | 2003/08/03 15:40 |
| 7 | IS&R | L7 | 2 | ("5753911").PN. | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/03 15:42 |
| 8 | BRS | L14 | 801 | 257/\$.ccls. and (silicon adj electrode) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/03 15:44 |
| 9 | BRS | L21 | 583 | 257/\$.ccls. and (silicon adj electrode) | USPAT | 2003/08/03 15:46 |
| 10 | BRS | L22 | 1556 | 257/\$.ccls. and (SOI adj substrate) | USPAT | 2003/08/03 15:51 |

| | Comments | Error Definition | Errors |
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| 1 | | | 0 |
| 2 | | | 0 |
| 3 | | | 0 |
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